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A journal on the chemical, electronic, optical and mechanical properties of glasses, amorphous semiconductors and metals, sol–gel materials, the liquid state of these solids and the processes by which they are formed

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The Journal of Non-Crystalline Solids publishes original research papers about oxide and non-oxide glasses, amorphous semiconductors, amorphous metals, glassy and amorphous films and coatings, glass-ceramics, glass composites, and processes by which these materials are produced. Papers about the liquid state are included insofar as the properties of the liquids are relevant to the formation of non-crystalline solids.

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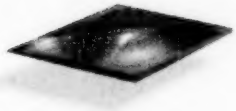

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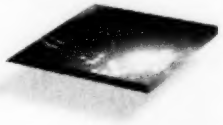

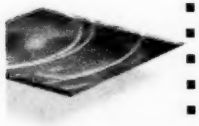

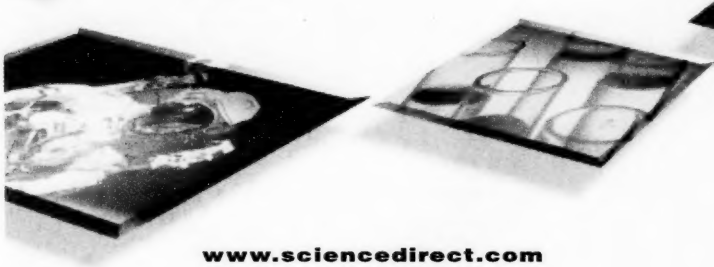

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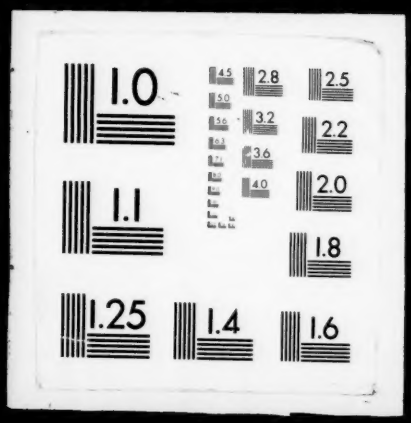
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